

ELECTRICAL CHARACTERISTIC (CHM4948JGP)

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-60			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$			-2	μA
I_{GSSF}	Gate-Body Leakage	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			+100	nA
I_{GSSR}	Gate-Body Leakage	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

ON CHARACTERISTICS (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-1		-3	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -3.1\text{ A}$		90	120	m Ω
		$V_{GS} = -4.5\text{ V}, I_D = -2.8\text{ A}$		120	150	
g_{FS}	Forward Transconductance	$V_{DS} = -15\text{ V}, I_D = -3.1\text{ A}$		7		S

SWITCHING CHARACTERISTICS (Note 4)

Q_g	Total Gate Charge	$V_{DS} = -30\text{ V}, I_D = -3.1\text{ A}$ $V_{GS} = -10\text{ V}$		21	29	nC
Q_{gs}	Gate-Source Charge			3		
Q_{gd}	Gate-Drain Charge			4		
t_{on}	Turn-On Time	$V_{DD} = -30\text{ V}$ $I_D = -1.0\text{ A}, V_{GS} = -10\text{ V}$ $R_{GEN} = 6\ \Omega$		13	45	nS
t_r	Rise Time			9	30	
t_{off}	Turn-Off Time			48	150	
t_f	Fall Time			22	75	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I_S	Drain-Source Diode Forward Current	(Note 1)			-2.0	A
V_{SD}	Drain-Source Diode Forward Voltage	$I_S = -2.0\text{ A}, V_{GS} = 0\text{ V}$ (Note 2)			-1.2	V